

650V Silicon Carbide Schottky Diode

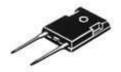
DESCRIPTION:

- Negligible reverse recovery
- · High Speed Switching
- · Positive temperature Coefficient
- Temperature Independent Switching
- RoHS Compliant

V_{RRM}	650V	
I _F	10A (TC=154°C)	
Qc	30nC	

TYPICAL APPLICATIONS:

- Switch mode power supplies
- · Solar inverters
- · Data Center
- Uninterruptible power supplies (UPS)



TO-247AC

MAXIMUM RATINGS (at T_C = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	650	V
Continuous Forward Current	Tc=25°C Tc=135°C Tc=154°C	I _F	32 15 10	А
Non-Repetitive Forward Surge Current	Tc=25°C , t_{P} =10ms, Half sine pulse Tc=110°C , t_{P} =10ms, Half sine pulse	I _{FSM}	92 88	А
Repetitive Peak Forward Surge Current	Tc=25°C, t _P =10ms, Half sine pulse	I _{FRM}	85	А
i ² t value	Tc=25 $^{\circ}$ C , t _P =10ms Tc=110 $^{\circ}$ C , t _P =10ms	∫ i ² dt	40 38	A ² S
Power dissipation	Tc=25°C Tc=110°C Tc=150°C	P _{tot}	130 56 21	W
Operation Junction temperature		Tj	-55~+175	$^{\circ}\!\mathbb{C}$
Storage temperature		T _{STG}	-55~+175	$^{\circ}\!\mathbb{C}$

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Typical	Unit
Thermal resistance, junction - case		R _{th(j-C)}	1.15	°C/W

ELECTRICAL CHARATERISTICS (at $T_C = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V _{DC}	650			V
Forward Voltage IF = 5A IF = 10A, Tc =25°C IF = 10A, Tc =175°C	V _F		1.17 1.37 1.66	1.6	>
Reverse Current $VR = 650V$, $Tc = 25^{\circ}C$ $VR = 650V$, $Tc = 175^{\circ}C$	I _R		5 12	60	uA
Total Capacitive Charge VR = 400V	Q _C		30		nC
Total capacitance VR = 1V, f =1MHz VR = 200V, f =1MHz VR = 400V, f =1MHz	С		455 57 56		pF
Capacitance Stored Energy VR = 400 V	Ec		4.9		uJ

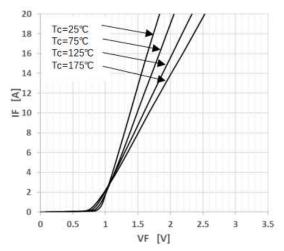


Figure 1. Forward characteristics

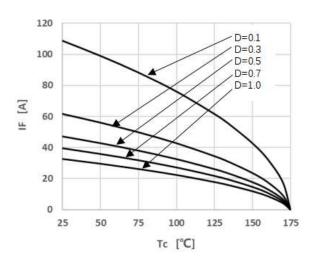


Figure 3. Peak Forward Current Derating

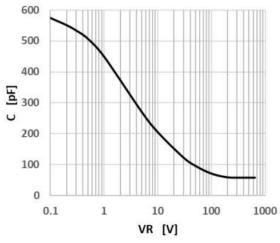


Figure 5. Capacitance vs. Reverse Voltage

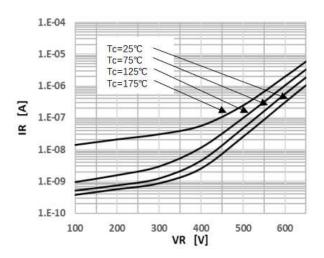


Figure 2. Reverse characteristics

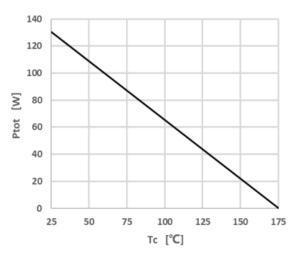


Figure 4. Power Dissipation

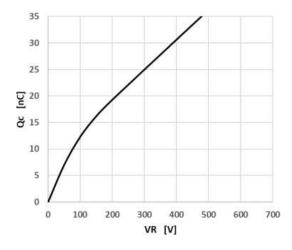
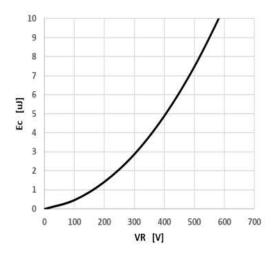


Figure 6. Capacitance Charge vs. Reverse Voltage





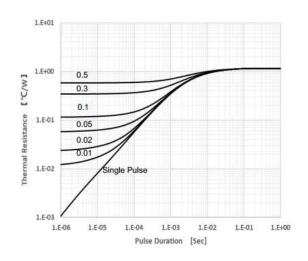
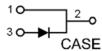
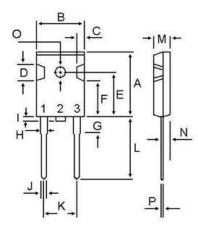


Figure 8. Transient Thermal Impedance

· Circuit diagram



• TO-247AC Package outlines : Dimensions in (mm)



DIM	MILLIMETERS		
DIIVI	MIN	MAX	
Α	20.63	22.38	
В	15.38	16.20	
С	1.90	2.70	
D	5.10	6.10	
E	14.81	15.22	
F	11.72	12.84	
G	3.75	4.35	
Н	1.82	2.46	
I		1.25	
J	0.89	1.53	
K	10.52	11.32	
L	18.50	21.50	
M	4.68	5.36	
N	2.40	2.80	
0	3.25	3.65	
Р	0.55	0.70	



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